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Applicants: Aratani et al.

Serial No.: 09/429,719

Title: Thin Film Formation Use Sputtering ...

Atty. Docket No. 9792486-0010 (formerly P99,2247)

Examiner: R. McDonald

Group Unit: 1753

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Response to First Office Action

In response to the First Office Action dated, 24 July 2000, the applicants respond as follows.

A. In the Claims:

1. (Amended) A method of forming a thin film comprising the step of: forming an AgPd alloy thin film using a sputtering target material, [wherein] the AgPd alloy thin film comprises Pd in an amount ranging from 0.5 to 4.9 atomic %, and irradiating an information recording layer with a light beam having a wavelength of less than or equal to 800 nm.

7. (Amended) A method of forming a thin film comprising the step of: forming an AgPdTi alloy thin film using a sputtering target material, [wherein] the AgPdTi alloy comprises Pd in an amount ranging from 0.1 to 1.5 atomic % and Ti in an amount ranging from 0.1 to 2.9 atomic %, and irradiating an information recording layer with a light beam having a wavelength of less than or equal to 800 nm.

8. (New) The method of claim 1, wherein the wavelength is less than or equal to 650 nm.

9. (New) The method of claim 2, wherein the wavelength is less than or equal to 650 nm.